

Consumer SSD E2000 Series

Introduction

Consumer SSD E2000 adopts M.2 interface, advanced SSD control computing chip and 3D NAND flash to effectively improve R/W speed and ensure data security.

It applies to personal computer and small-size proxy server to providing stable and high-speed service. It can also improve the high-end gaming experience and 3D graphics editing performance.



Available Models

HS-SSD-E2000 / 256GB

HS-SSD-E2000 / 512GB

HS-SSD-E2000 / 1024GB

HS-SSD-E2000 / 2048GB

Typical Application

- PC (notebook and desktop)
- Small-size proxy sever

Features and Functions

High R/W Speed

Supports PCIe and NVMe Max. read speed up to 3500 MB/s

3D NAND

Adopts 3D NAND flash to optimize capacity, performance and stability

Shockproof

No mechanical structure Adopts electronic chips control High data security

M.2 Interface





Specifications

Model		HS-SSD-E2000			
Capacity		256 GB	512 GB	1024 GB	2048GB
Form Factor		M.2 (NGFF)			
Interface		PCIe Gen 3 x 4, NVMe			
DRAM Cache Memory		256 MB	512MB	1 GB	2GB
Dimensions		80.15 mm × 22.15 mm × 2.38 mm			
Max. sequential 128 K read speed 1		3100 MB/s	3300 MB/s	3500 MB/s	3500 MB/s
Max. sequential 128 K write speed		1300 MB/s	2100 MB/s	3000 MB/s	2750 MB/s
Max. random 4 K read IOPS		187 K	369 K	600 K	500 K
Max. random 4 K write IOPS		245 K	470 K	600 K	513 K
Power consumption	Read (RMS max.)	6.4 W	7 W	7.2 W	5.9 W
	Write (RMS max.)	3.9 W	5 W	6.1 W	6.1 W
Endurance (TBW)		380 TB	800 TB	1665 TB	3300 TB
NAND flash memory		3D TLC			
Weight		≤ 8 g (not include the weight of metal casing, heat dispersion silicone and other accessories)			
MTBF (Mean Time between Failures)		1,500,000 h			
Operation temperature		0 °C to 70 °C (32 °F to 158 °F)			
Storage temperature		-40 °C to +85 °C (-40 °F to +185 °F)			
Operation humidity		5% to 95% (no condensation)			
Limited warranty period		3 years			

^{*:} Performance test is performed in a specific testing environment. Any change of computer system, operation system, hardware, software, or functions will influence the test result.





Headquarters

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- **1 2**: Performance in the specifications is tested based on CrystalDiskMark.
- 3: Power consumption may differ according to flash configuration and platform. Power consumptions are measured by using CrystalDiskMark 1000 MB to test sequential R/W 5 times. Power consumptions are measured when sequential Read [1/5] to [5/5] and sequential Write [1/5] to [5/5].
- 4: The TBW value is calculated based on Workload of JEDC 218B/219A standard.
- **5**: The MTBF value is calculated based on the functional failure rate of JEDC 218B/219A standard.